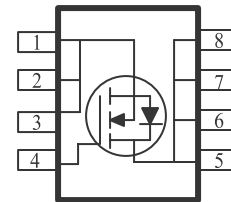
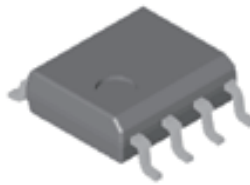


N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology



PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
30	6 @ $V_{GS} = 10V$	18.6
	8 @ $V_{GS} = 4.5V$	16.1

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	20	
Continuous Drain Current ^a	$T_A = 25^\circ C$	I_D	18.6	A
	$T_A = 70^\circ C$		15.7	
Pulsed Drain Current ^b		I_{DM}	60	
Continuous Source Current (Diode Conduction) ^a		I_S	2.9	A
Power Dissipation ^a	$T_A = 25^\circ C$	P_D	3.1	W
	$T_A = 70^\circ C$		2.2	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ C$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	$R_{\theta JA}$	40	$^\circ C/W$
	Steady State		80	$^\circ C/W$

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 uA	1		3	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V			100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1	uA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55°C			5	
On-State Drain Current ^A	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	30			A
Drain-Source On-Resistance ^A	r _{DS(on)}	V _{GS} = 10 V, I _D = 18.6 A			6	mΩ
		V _{GS} = 4.5 V, I _D = 16.1 A			8	
Forward Tranconductance ^A	g _{fs}	V _{DS} = 15 V, I _D = 18.6 A		90		S
Diode Forward Voltage	V _{SD}	I _S = 2.3 A, V _{GS} = 0 V		0.7		V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 18.6 A		25		nC
Gate-Source Charge	Q _{gs}			6		
Gate-Drain Charge	Q _{gd}			9		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 6 Ω , ID = 1 A, VGEN = 10 V		20		nS
Rise Time	t _r			13		
Turn-Off Delay Time	t _{d(off)}			82		
Fall-Time	t _f			43		

Notes

- Pulse test: PW ≤ 300us duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

Typical Electrical Characteristics (N-Channel)

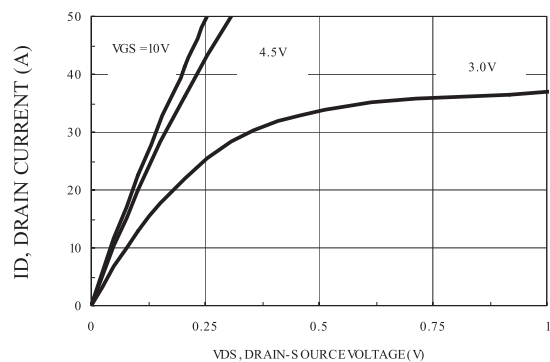


Figure 1. Output Characteristics

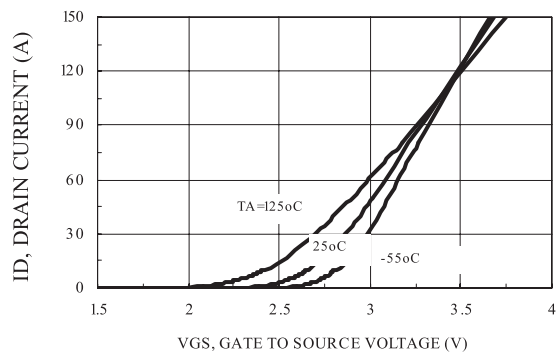


Figure 2. Transfer Characteristics

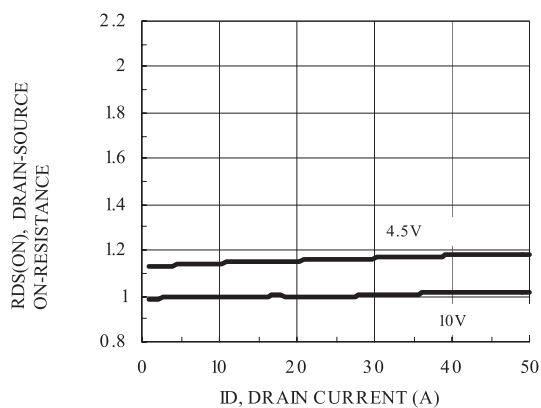


Figure 3. On-Resistance vs. Drain Current

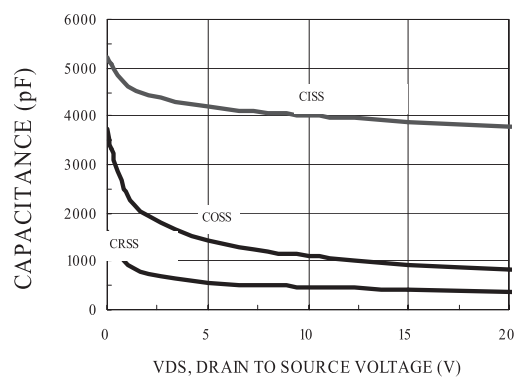


Figure 4. Capacitance

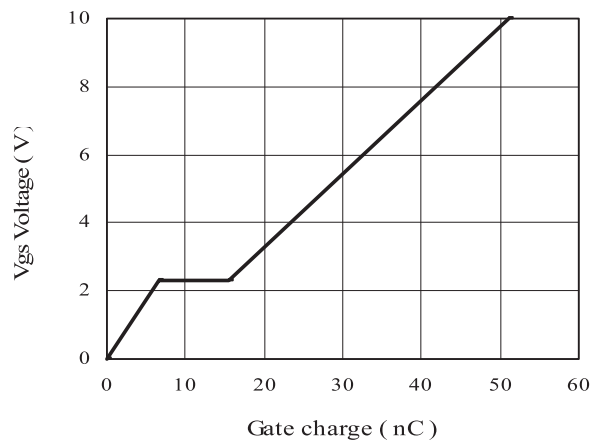


Figure 5. Gate Charge

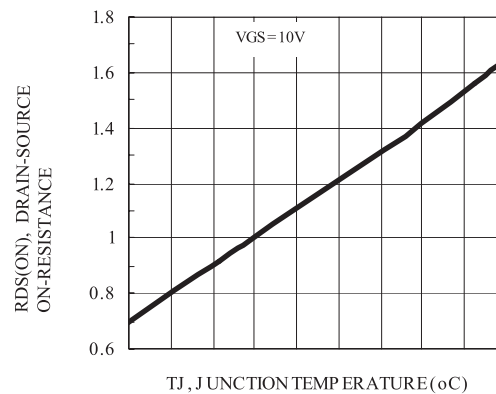


Figure 6. On-Resistance vs. Junction Temperature

Typical Electrical Characteristics (N-Channel)

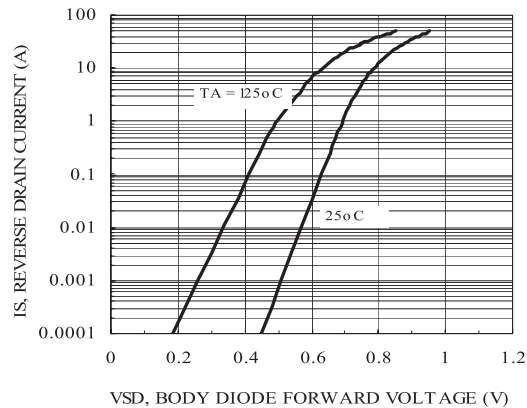


Figure 7. Source-Drain Diode Forward Voltage

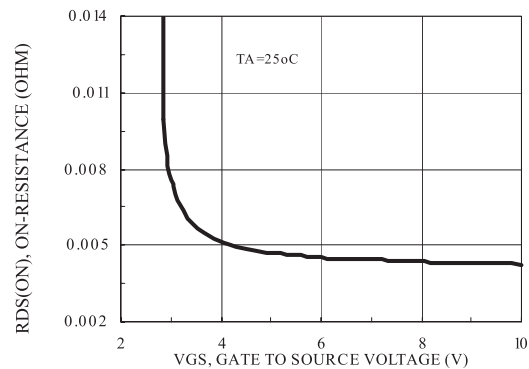


Figure 8. On-Resistance vs. Gate-to-Source Voltage

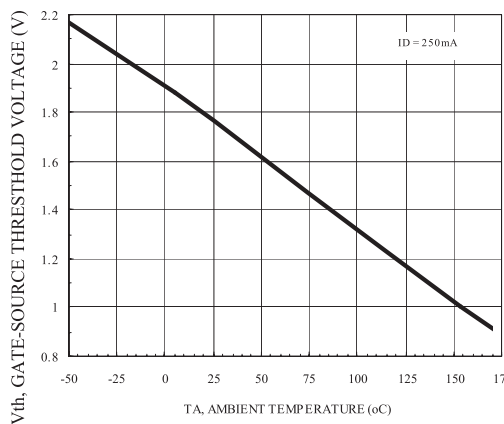


Figure 9. Threshold Voltage

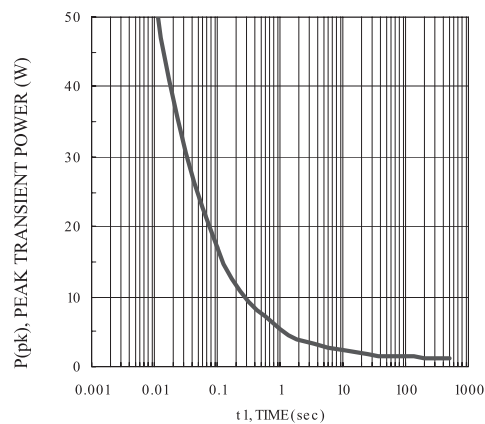
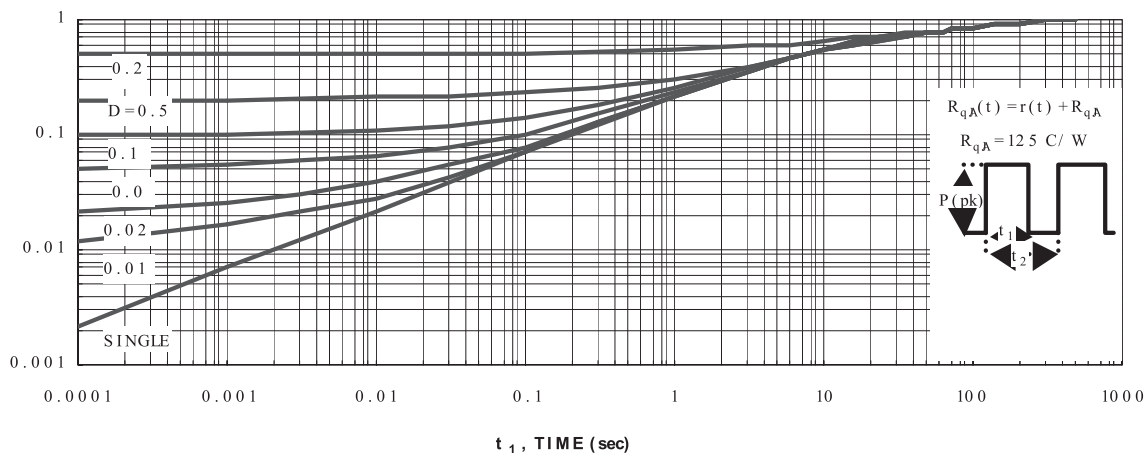


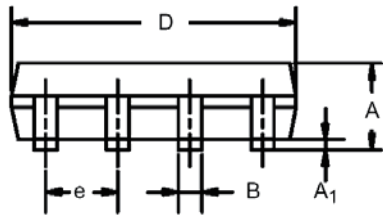
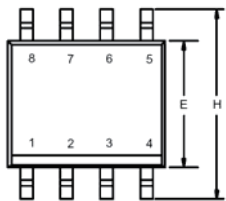
Figure 10. Single Pulse Power

Figure 11. Normalized Thermal Transient Impedance, Junction-to-Ambient



Package Information

SO-8: 8LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

